Technical Data Data Sheet 760, Rev.-

# Ultra Fast T<sub>rr</sub> < 7 nsec

## SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop

### **Applications:**

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

#### **Maximum Ratings**<sup>(1)</sup>:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V <sub>RWM</sub>	-	200	V
Max. Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle, rectangular wave form	1	A
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave <sup>(1)</sup>	20	A
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	$T_J = 25 \ ^{\circ}C, I_{AS} = 0.13A, L = 40mH$	2.8	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 µs f limited by T <sub>J</sub> max V <sub>A</sub> =1.5V <sub>R</sub>	0.13	А
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	T <sub>stg</sub>	-	-65 to +200	°C

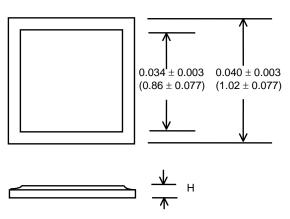
#### **Electrical Characteristics**<sup>(1)</sup>:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 1A, Pulse, T <sub>J</sub> = 25 °C	0.92	V
	$V_{F2}$	@ 1A, Pulse, T <sub>J</sub> = 125 °C	0.76	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 200V, Pulse,	30	μA
		T <sub>J</sub> = 25 °C		
	I <sub>R2</sub>	@V <sub>R</sub> = 200V, Pulse,	0.6	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C	20	pF
		f <sub>SIG</sub> = 1MHz,		
		V <sub>SIG</sub> = 50mV (p-p)		
Max. Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A,	7	nsec
		I <sub>RM</sub> = 0.25 A, T <sub>J</sub> = 25 °C		

(1) in SHD package

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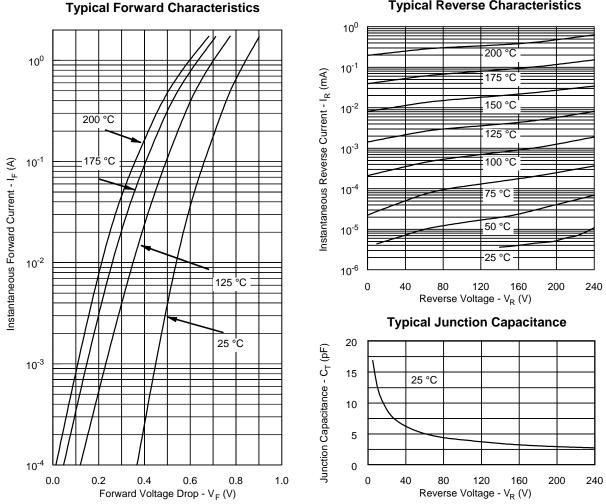


Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization AI - 25 kÅ minimum or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

Dimension H =  $0.0105 \pm 0.001 (0.27 \pm 0.026)$  for AI top; Dimension H = 0.0155  $\pm$  0.001 (0.39  $\pm$  0.026) for Ag top.



**Typical Reverse Characteristics** 

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